

# RGTVX6TS65

# 650V 80A Field Stop Trench IGBT

$V_{CES}$	650V
I <sub>C(100°C)</sub>	80A
V <sub>CE(sat) (Typ.)</sub>	1.5V
$P_D$	404W

### Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching & Low Switching Loss
- 3) Short Circuit Withstand Time 2µs
- 4) Pb free Lead Plating; RoHS Compliant

# Applications

Solar Inverter

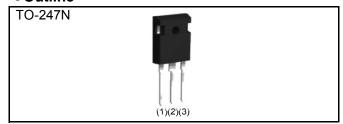
**UPS** 

Welding

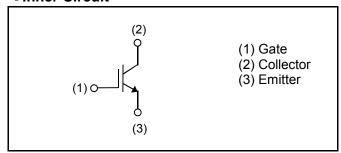
ΙH

**PFC** 

### Outline



## ●Inner Circuit



## Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Typo	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTVX6TS65

# ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	650	V
Gate - Emitter Voltage		$V_{GES}$	±30	V
Collector Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	144	А
Collector Current	T <sub>C</sub> = 100°C	I <sub>C</sub>	80	А
Pulsed Collector Current		I <sub>CP</sub> *1	320	А
T <sub>C</sub> = 25°C		P <sub>D</sub>	404	W
Power Dissipation $T_C = 100^{\circ}C$		P <sub>D</sub>	202	W
Operating Junction Temperature		T <sub>j</sub>	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>imax</sub>.

## ●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei		Min.	Тур.	Max.	
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.37	°C/W

# ullet IGBT Electrical Characteristics (at $T_j$ = 25°C unless otherwise specified)

Parameter	Parameter Symbol Cond	Conditions	Values			Unit
r ai ainietei		Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	-	1	V
Collector Cut - off Current	I <sub>CES</sub>	V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V	1	1	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	ı	ı	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 57.1 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_C$ = 80A, $V_{GE}$ = 15V $T_j$ = 25°C $T_j$ = 175°C	-	1.5 1.85	1.9 -	V

# ullet IGBT Electrical Characteristics (at $T_j$ = 25°C unless otherwise specified)

Parameter Symbol		Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input Capacitance	$C_{\text{ies}}$	V <sub>CE</sub> = 30V	-	4810	-	
Output Capacitance	C <sub>oes</sub>	V <sub>GE</sub> = 0V	-	184	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	79	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 400V	-	171	-	
Gate - Emitter Charge	$Q_{ge}$	I <sub>C</sub> = 80A	-	33	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	59	-	
Turn - on Delay Time	t <sub>d(on)</sub>	I <sub>C</sub> = 80A, V <sub>CC</sub> = 400V	-	45	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	29	-	20
Turn - off Delay Time	$t_{d(off)}$	T <sub>j</sub> = 25°C	-	201	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	34	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> includes diode	-	2.65	-	
Turn - off Switching Loss	$E_{off}$	reverse recovery	-	1.80	-	mJ
Turn - on Delay Time	t <sub>d(on)</sub>	I <sub>C</sub> = 80A, V <sub>CC</sub> = 400V	-	49	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	34	-	20
Turn - off Delay Time	$t_{d(off)}$	T <sub>j</sub> = 175°C	-	218	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	80	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> includes diode	-	2.74	-	m l
Turn - off Switching Loss	$E_{off}$	reverse recovery	-	2.31	-	mJ
		I <sub>C</sub> = 320A, V <sub>CC</sub> = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FU	LL SQUA	RE	-
		$R_G = 100\Omega, T_j = 175^{\circ}C$				
		$V_{CC} \le 360V$				
Short Circuit Withstand Time	$t_{sc}$	V <sub>GE</sub> = 15V	2	-	-	μs
		T <sub>j</sub> = 25°C				

### **•**Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

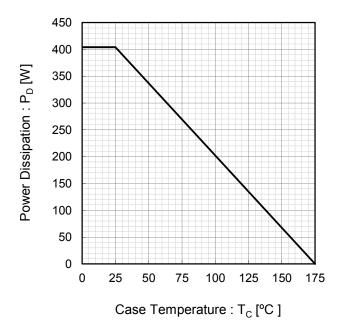


Fig.2 Collector Current vs. Case Temperature

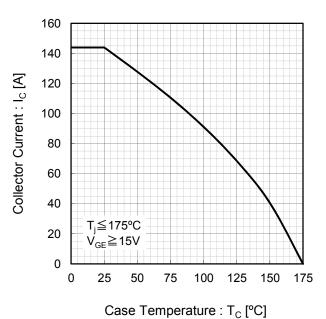


Fig.3 Forward Bias Safe Operating Area

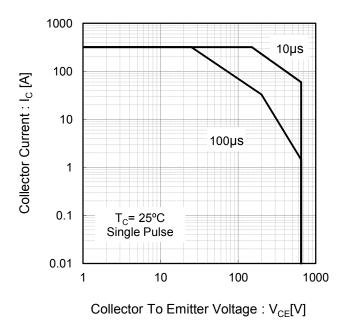
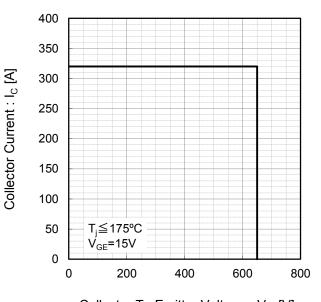


Fig.4 Reverse Bias Safe Operating Area



### Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

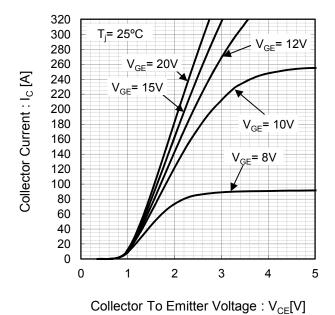
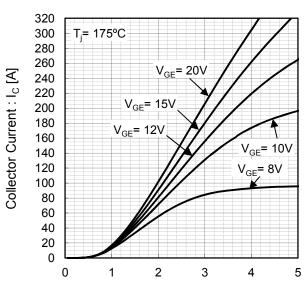


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.7 Typical Transfer Characteristics

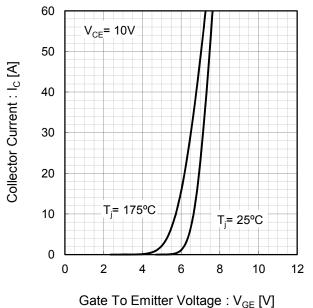
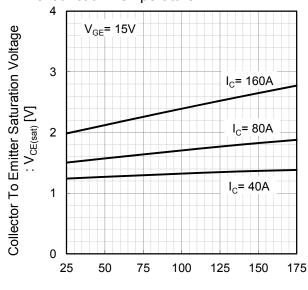


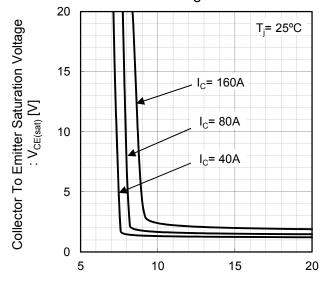
Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T<sub>i</sub> [°C]

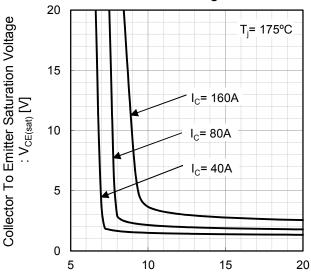
### Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

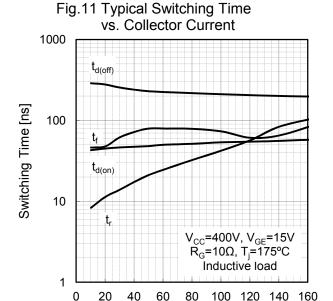


Gate To Emitter Voltage : V<sub>GE</sub> [V]

Fig. 10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V<sub>GE</sub> [V]



Collector Current : I<sub>C</sub> [A]

Fig.12 Typical Switching Time vs. Gate Resistance

1000  $t_{d(off)}$ 100  $t_{d(off)}$   $t_{d(on)}$   $t_{d$ 

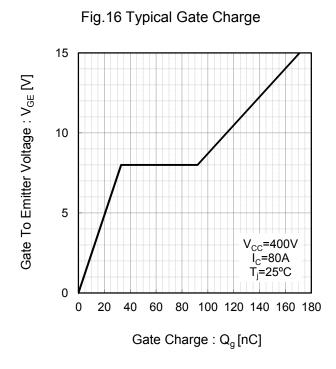
### • Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ]  $E_{off}$ 1 0.1  $V_{CC}$ =400V,  $V_{GE}$ =15V  $R_{G}$ =10 $\Omega$ ,  $T_{j}$ =175°C Inductive load 0.01 0 20 100 120 140 160 40 60 Collector Current : I<sub>C</sub> [A]

vs. Gate Resistance vs. Gate Resistance 10  $E_{on}$  1  $E_{off}$  0.1  $V_{cc}=400V, I_{c}=80A$   $V_{GE}=15V, T_{j}=175^{\circ}C$  Inductive load 0.01 0 10 20 30 40 50 Gate Resistance :  $R_{G}[\Omega]$ 

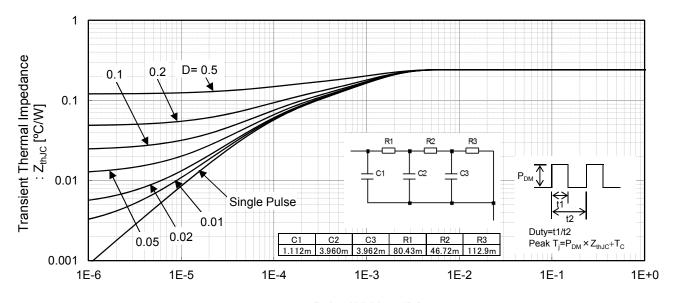
Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V<sub>GE</sub>=0V T,=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V<sub>CE</sub>[V]



## **•**Electrical Characteristic Curves

Fig.17 Typical IGBT Transient Thermal Impedance



Pulse Width: t1[s]

# ●Inductive Load Switching Circuit and Waveform

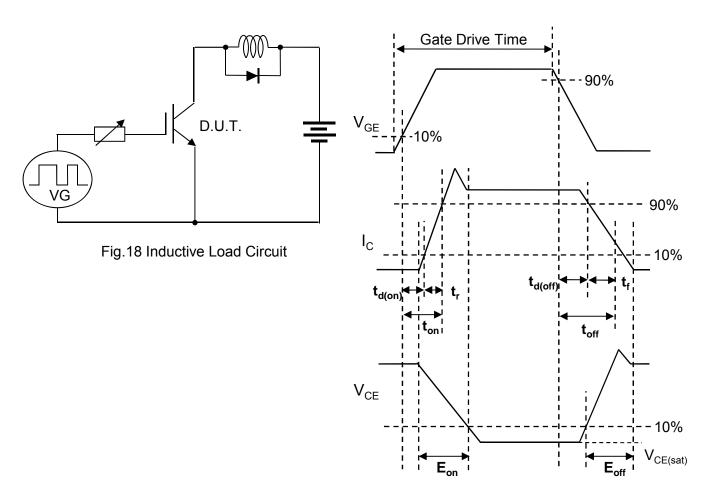


Fig.19 Inductive Load Waveform

#### Notes

- 1) The information contained herein is subject to change without notice.
- Before you use our Products, please contact our sales representative and verify the latest specifications:
- 3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors. Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM
- 4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.
- 5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.
- 6) The Products are intended for use in general electronic equipment (i.e. AV/OA devices, communication, consumer systems, gaming/entertainment sets) as well as the applications indicated in this document.
- 7) The Products specified in this document are not designed to be radiation tolerant.
- 8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative : transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.
- 9) Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.
- 10) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.
- 11) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.
- 12) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.
- 13) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.
- 14) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM.



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

# ROHM Customer Support System

http://www.rohm.com/contact/



# RGTVX6TS65 - Web Page

**Distribution Inventory** 

Part Number	RGTVX6TS65
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes